Thyristors BT152B series

## **GENERAL DESCRIPTION**

#### Glass passivated thyristors in a plastic envelope suitable surface for mounting, intended for use in applications requiring high bidirectional voltage blocking capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

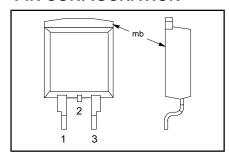
## **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V <sub>DRM</sub> , V <sub>RRM</sub> I <sub>T(AV)</sub> I <sub>T(RMS)</sub> I <sub>TSM</sub>	BT152B- Repetitive peak off-state voltages Average on-state current RMS on-state current Non-repetitive peak on-state current	400R 450 13 20 200	600R 650 13 20 200	800R 800 13 20 200	V A A A

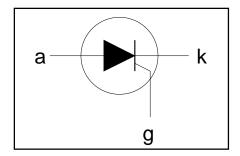
## **PINNING - SOT404**

PIN	DESCRIPTION		
1	cathode		
2	anode		
3	gate		
mb	anode		

### PIN CONFIGURATION



### **SYMBOL**



## LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT	
$V_{DRM}$	Repetitive peak off-state voltages		-	<b>-400R</b> 450 <sup>1</sup>	<b>-600R</b> 650 <sup>1</sup>	<b>-800R</b> 800	V
$\begin{matrix} I_{T(AV)} \\ I_{T(RMS)} \\ I_{TSM} \end{matrix}$	Average on-state current RMS on-state current Non-repetitive peak on-state current	half sine wave; $T_{mb} \le 103$ °C all conduction angles half sine wave; $T_j = 25$ °C prior to surge	-		13 20		A A
		t = 10 ms t = 8.3 ms	-		200 220		A A
l²t dl <sub>⊤</sub> /dt	I <sup>2</sup> t for fusing Repetitive rate of rise of on-state current after triggering	t = 10  ms $I_{TM} = 50 \text{ A}; I_G = 0.2 \text{ A};$ $dI_G/dt = 0.2 \text{ A}/\mu\text{s}$	-		200 200		A <sup>2</sup> s A/μs
$V_GM$	Peak gate current Peak gate voltage		- -		5 5		A V
V <sub>RGM</sub> P <sub>GM</sub> P <sub>G(AV)</sub>	Peak reverse gate voltage Peak gate power Average gate power	over any 20 ms period	-		5 20 0.5		W W
T <sub>stg</sub>	Storage temperature Operating junction temperature		-40 -		150 125		ပဲ့

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<sup>1</sup> Although not recommended, off-state voltages up to 800V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15  $A/\mu s$ .

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# THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R <sub>th j-mb</sub>	Thermal resistance		-	-	1.1	K/W
R <sub>th i-a</sub>	junction to mounting base Thermal resistance junction to ambient	minimum footprint, FR4 board	-	55	-	K/W

## STATIC CHARACTERISTICS

 $T_i = 25$  °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>GT</sub>	Gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$	-	3	32	mΑ
I <sub>L</sub>	Latching current	$V_{\rm D} = 12 \text{ V}; I_{\rm GT} = 0.1 \text{ A}$	-	25	80	mΑ
I <sub>H</sub>	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	15	60	mΑ
ĺΫ́	On-state voltage	$I_T = 40 \text{ A}$	-	1.4	1.75	V
V <sub>GT</sub>	Gate trigger voltage	$\dot{V}_{D} = 12 \text{ V}; I_{T} = 0.1 \text{ A}$	-	0.6	1.5	V
		$V_D = V_{DRM(max)}$ ; $I_T = 0.1 \text{ A}$ ; $T_j = 125 ^{\circ}\text{C}$	0.25	0.4	-	V
I <sub>D</sub> , I <sub>R</sub>	Off-state leakage current	$V_D = V_{DRM(max)}$ ; $V_R = V_{RRM(max)}$ ; $T_j = 125$ °C	-	0.2	1.0	mΑ

## **DYNAMIC CHARACTERISTICS**

 $T_i = 25$  °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV <sub>D</sub> /dt	Critical rate of rise of off-state voltage	V <sub>DM</sub> = 67% V <sub>DRM(max)</sub> ; T <sub>j</sub> = 125 °C; exponential waveform gate open circuit	200	300	-	V/μs
t <sub>gt</sub>	Gate controlled turn-on	$V_D = V_{DRM(max)}$ ; $I_G = 0.1$ Å; $dI_G/dt = 5$ A/ $\mu$ s; $I_{TM} = 40$ Å	-	2	-	μs
t <sub>q</sub>	Circuit commutated turn-off time	$V_D = 67\% \ V_{DRM(max)}; T_j = 125 \ ^{\circ}C; I_{TM} = 50 \ A; V_R = 25 \ V; dI_{TM}/dt = 30 \ A/\mu s; dV_D/dt = 50 \ V/\mu s; R_{GK} = 100 \ \Omega$	-	70	-	μs

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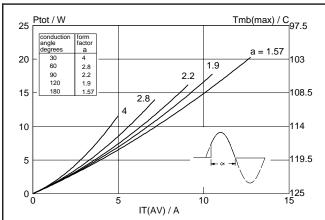


Fig.1. Maximum on-state dissipation,  $P_{tot}$ , versus average on-state current,  $I_{T(AV)}$ , where  $a = form\ factor = I_{T(RMS)}/I_{T(AV)}$ .

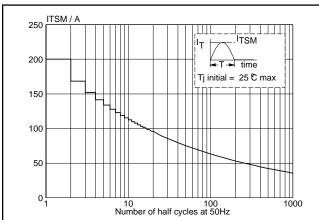


Fig.4. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus number of cycles, for sinusoidal currents, f = 50 Hz.

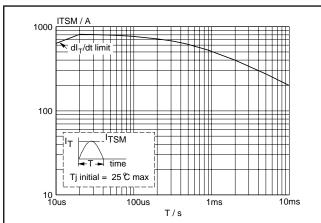


Fig.2. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus pulse width  $t_p$ , for sinusoidal currents,  $t_p \le 10$ ms.

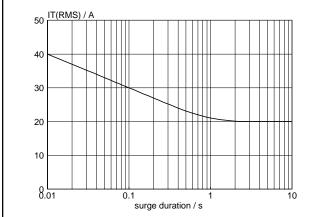


Fig.5. Maximum permissible repetitive rms on-state current  $I_{T(RMS)}$ , versus surge duration, for sinusoidal currents, f = 50 Hz;  $T_{mb} \le 103$  °C.

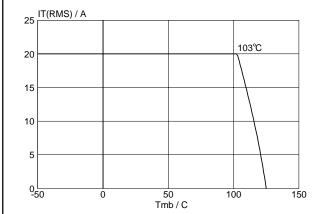
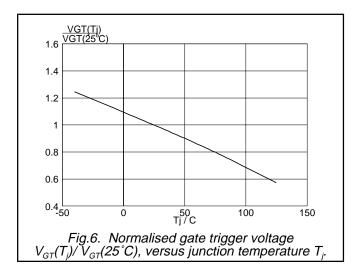
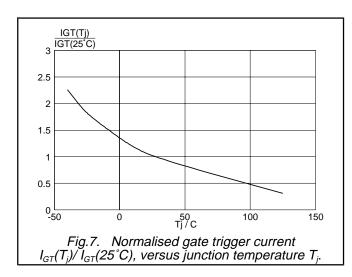
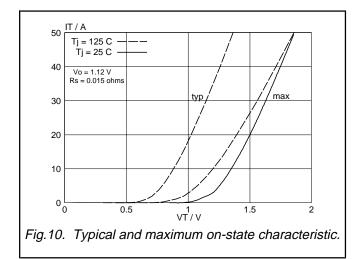


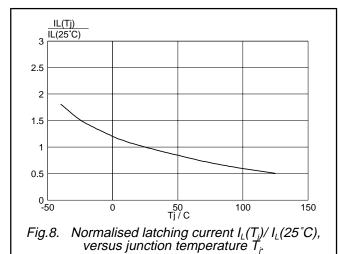
Fig.3. Maximum permissible rms current  $I_{T(RMS)}$ , versus mounting base temperature  $T_{mb}$ .

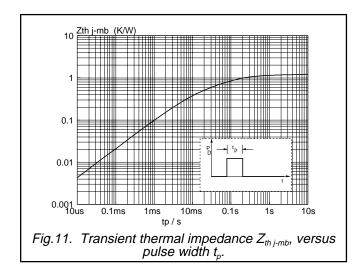


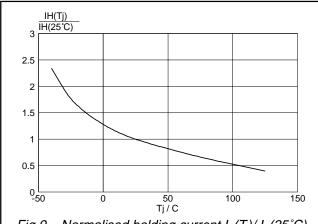
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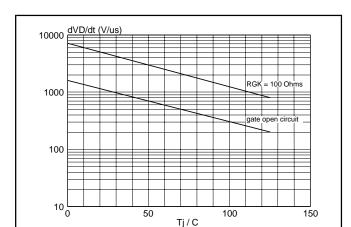
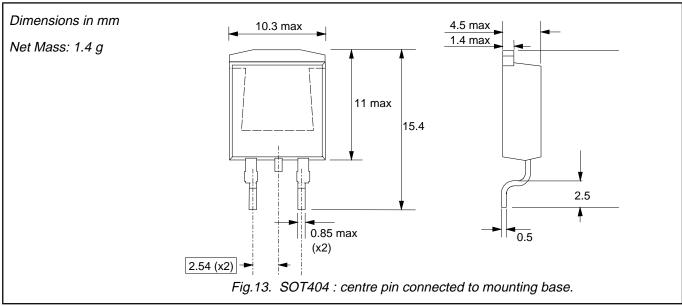


Fig.9. Normalised holding current  $I_H(T_i)/I_H(25^{\circ}C)$ , versus junction temperature  $T_j$ .

Fig.12. Typical, critical rate of rise of off-state voltage, dV<sub>D</sub>/dt versus junction temperature T<sub>i</sub>.

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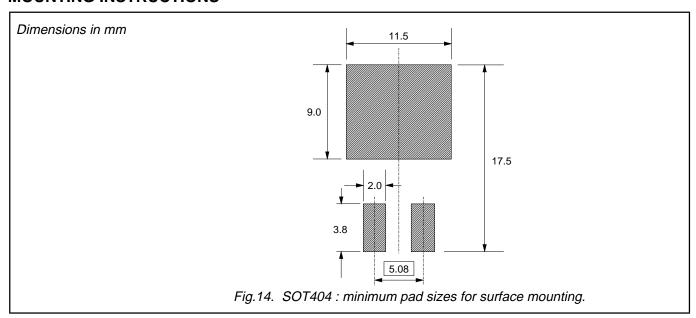
## **MECHANICAL DATA**



### **Notes**

1. Epoxy meets UL94 V0 at 1/8".

## **MOUNTING INSTRUCTIONS**



## **Notes**

1. Plastic meets UL94 V0 at 1/8".

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### **DEFINITIONS**

Data sheet status					
Objective specification	This data sheet contains target or goal specifications for product development.				
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.				
Product specification	This data sheet contains final product specifications.				
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### Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

#### **Application information**

Where application information is given, it is advisory and does not form part of the specification.

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